

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD1265 2SD1265A

DESCRIPTION

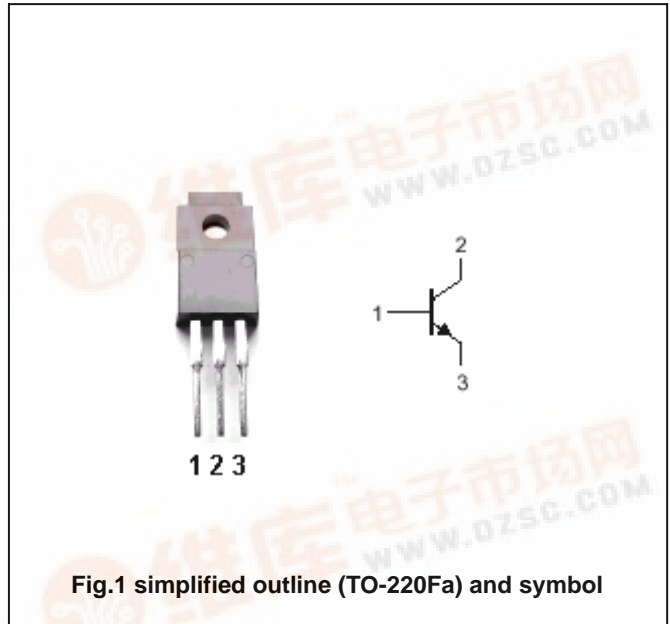
- With TO-220Fa package
- Low collector saturation voltage
- Wide area of safe operation

APPLICATIONS

- For audio frequency power applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SD1265	60	V
		2SD1265A	80	
V <sub>CEO</sub>	Collector-emitter voltage	2SD1265	60	V
		2SD1265A	80	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	8	V
I <sub>C</sub>	Collector current (DC)		4	A
I <sub>CM</sub>	Collector current-peak		6	A
I <sub>B</sub>	Base current		1	A
P <sub>C</sub>	Collector power dissipation	T <sub>c</sub> =25°C	30	W
		T <sub>a</sub> =25°C	2	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	2SD1265	60			V
		2SD1265A	80			
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.4A			1.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =1A; V <sub>CE</sub> =3V			1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =20V; I <sub>E</sub> =0			30	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =8V; I <sub>C</sub> =0			1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.1A; V <sub>CE</sub> =3V	40			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =3V	30		160	

◆ h<sub>FE-2</sub> Classifications

Q	P	O
30-60	500-100	80-160

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PACKAGE OUTLINE

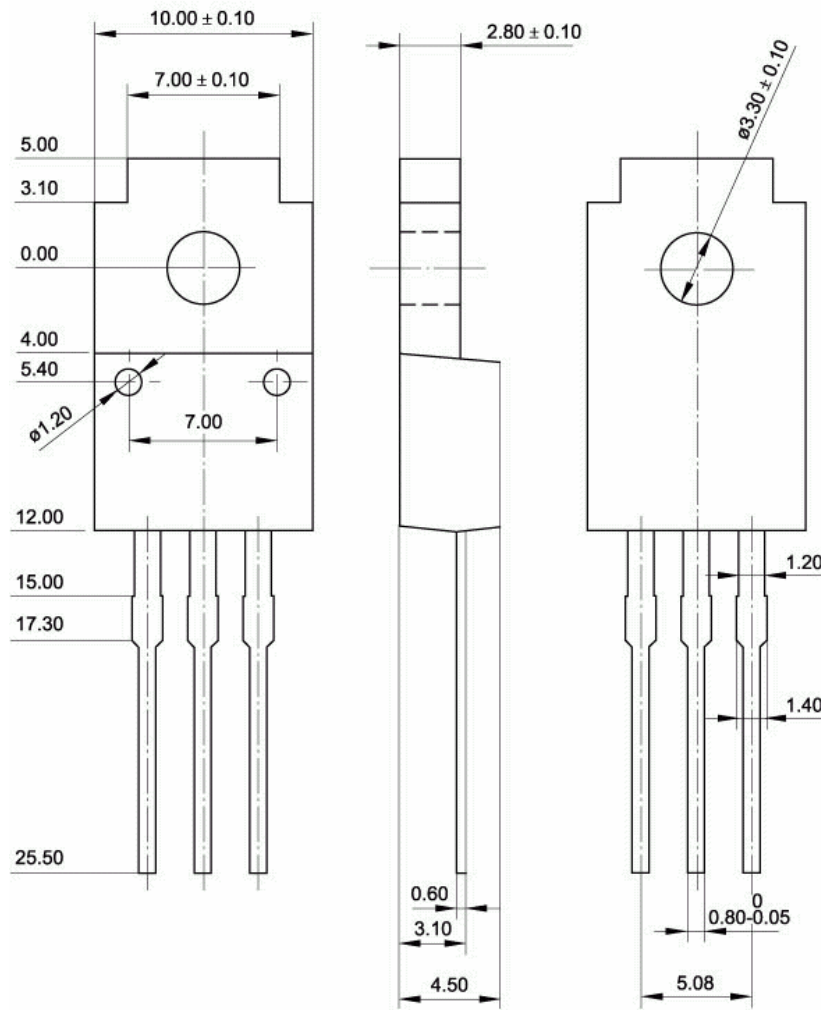


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)